

Customer No.: 31561  
Application No: 10/719,593  
Docket No.:15866-US-PA

In the Claims:

Please amend the claims according to the following listing of claims and substitute it for all prior versions and listings of claims in the application.

1. (currently amended) A method for detecting electrostatic charges on a wafer surface, comprising the steps of:
  - (a) disposing a capacitor plate above a wafer surface on which electrostatic charges are to be scanned, wherein the capacitor plate comprises a plurality of capacitor sub-plates electrically insulated from each other;
  - (b) using a movable probe to measure voltages at various locations at the capacitor plate;
  - (c) collecting the measured voltage distribution; and
  - (d) examining the collected voltage distribution to identify areas on the wafer surface correspondingly to high electrostatic charge density.
2. (original) The method for detecting electrostatic charges on a wafer surface according to claim 1, wherein the wafer contains a dielectric layer at its outmost surface.
3. (original) The method for detecting electrostatic charges on a wafer surface according to claim 2, wherein the dielectric layer is an oxide layer.
4. (original) The method for detecting electrostatic charges on a wafer surface according to claim 1, wherein the method is performed following a cleansing step using pure water or de-ionized water to remove particles or other impurities on the wafer surface.
5. (original) The method for detecting electrostatic charges on a wafer surface according to claim 1, wherein the capacitor plate is structured such that it can be moved both vertically and horizontally above the wafer surface.

Customer No.: 31561  
Application No: 10/719,593  
Docket No.:15866-US-PA

6. (cancelled)
7. (currently amended) A method for detecting electrostatic charges on a wafer surface, comprising the steps of:
  - (a) disposing a capacitor plate above a wafer surface on which electrostatic charges are to be scanned, wherein the capacitor plate comprises a plurality of capacitor sub-plates electrically insulated from each other;
  - (b) attaching a probe on the capacitor plate;
  - (c) moving the capacitor plate horizontally above the wafer surface so as to allow the probe to measure voltages at various locations above the wafer surface;
  - (d) collecting the measured voltage distribution; and
  - (e) examining the collected voltage distribution to identify areas on the wafer surface correspondingly to high electrostatic charge density.
8. (original) The method for detecting electrostatic charges on a wafer surface according to claim 7, wherein the wafer contains a dielectric layer at its outmost surface.
9. (original) The method for detecting electrostatic charges on a wafer surface according to claim 8, wherein the dielectric layer is an oxide layer.
10. (original) The method for detecting electrostatic charges on a wafer surface according to claim 7, wherein the method is performed following a cleansing step using pure water or de-ionized water to remove particles or other impurities on the wafer surface.
11. (original) The method for detecting electrostatic charges on a wafer surface according to claim 7, wherein the capacitor plate is structured such that it can be moved both vertically

Customer No.: 31561  
Application No: 10/719,593  
Docket No.:15866-US-PA

and horizontally above the wafer surface.

12. (currently amended) An apparatus method for detecting electrostatic charges on a wafer surface, comprising the steps of:

- (a) movable capacitor plate to be placed above a wafer surface on which electrostatic charges are to be scanned, wherein the capacitor plate comprises a plurality of capacitor sub-plates electrically insulated from each other;
- (b) a movable probe to measure voltages at various locations at the capacitor plate; and
- (c) a recorder to collect and record the measured voltage distribution.

13. (original) The apparatus for detecting electrostatic charges on a wafer surface according to claim 12, wherein the wafer contains a dielectric layer at its outmost surface.

14. (original) The apparatus for detecting electrostatic charges on a wafer surface according to claim 13, wherein the dielectric layer is an oxide layer.

15. (original) The apparatus for detecting electrostatic charges on a wafer surface according to claim 12, which is to be performed following a cleansing step using pure water or de-ionized water to remove particles or other impurities on the wafer surface.

16. (original) The apparatus for detecting electrostatic charges on a wafer surface according to claim 12, wherein the capacitor plate is structured such that it can be moved both vertically and horizontally above the wafer surface.

17. (cancelled)